

ESD NOISE CLIPPING DIODES

NNCD5.6LG to NNCD6.8LG

LOW CAPACITANCE TYPE ELECTROSTATIC DISCHARGE NOISE CLIPPING DIODES (QUARTO TYPE: COMMON ANODE) 5-PIN MINI MOLD

This product series is a low capacitance type diode developed for ESD (Electrostatic Discharge) absorption. Based on the IEC1000-4-2 test on electromagnetic interference (EMI), the diode assures an endurance of no less than 8 kV, and capacitance is small with 10 pF between the terminal. This product series is the most suitable for the ESD absorption in the high-speed data communication bus such as USB.

With four elements mounted in the 5Pin Mini Mold Package, that product can cope with high density assembling.

FEATURES

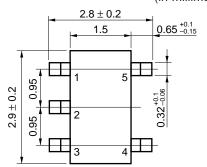
- · Based on the electrostatic discharge immunity test (IEC1000-4-2), the product assures the minimum endurance of 8 kV.
- Capacitance is small with 10 pF (at VR = 0 V, f = 1 MHz) between the terminal. It is excellent in the frequency characteristic.
- With 4 elements mounted (common anode) in the 5-pin mini mold package, that product can cope with high density assembling.

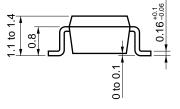
APPLICATIONS

 External interface circuit ESD absorption in the high-speed data communication bus such as USB.

PACKAGE DIMENSIONS

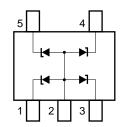
(in millimeters)





(5-pin mini mold)

PIN CONNECTION



- 1: K1 Cathode 1
- Anode (Common)
- 3: K2 Cathode 2
- 4: K3 Cathode3
- 5: K4 Cathode4

MAXIMUM RATINGS ($T_A = 25^{\circ}C$)

Junction Temperature

200 mW **Power Dissipation** (Total) P_RSM Surge Reverse Power $2W (t = 10 \mu s, 1 \text{ pulse})$ Fig.5

150°C

Τį Storage Temperature -55°C to +150°C Tstq



ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$) (A-K1, A-K2, A-K3, A-K4)

| Type No | Breakdown Voltage ^{Note 1} V _{BR} (V) | | | Dynamic Note 2 Impedance $Z_z(\Omega)$ | | Reverse Leakage I _R (µA) | | Capacitance Ct (pF) | | ESD Voltage ^{Note 3} (kV) | |
|-----------|--|------|---------|--|---------|---|--------------------|------------------------|-----------------------------------|------------------------------------|---|
| | MIN. | MAX. | I⊤ (mA) | MAX. | I⊤ (mA) | MAX. | V _R (V) | TYP. | Test Condition | MIN. | Test Condition |
| NNCD5.6LG | 5.3 | 6.3 | 5 | 80 | 5 | 5 | 2.5 | 10 | V _R = 0 V f = 1 MHz | 8 | $\begin{array}{c} C = 150 \text{ pF} \\ R = 330 \Omega \\ \text{Contact} \\ \text{discharge} \end{array}$ |
| NNCD6.2LG | 5.7 | 6.7 | 5 | 50 | 5 | 2 | 3.0 | 8 | | 8 | |
| NNCD6.8LG | 6.2 | 7.1 | 5 | 30 | 5 | 2 | 3.5 | 7 | | 8 | |

Notes 1. Tested with pulse (40 ms)

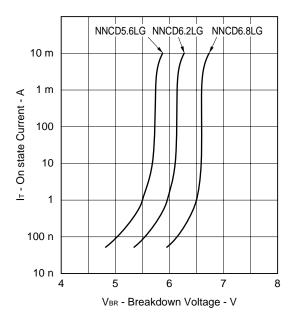
- 2. Z_z is measured at I_T given a small A.C. signal.
- 3. ESD voltage is measured based on the IEC1000-4-2 test on electromagnetic interference (EMI).

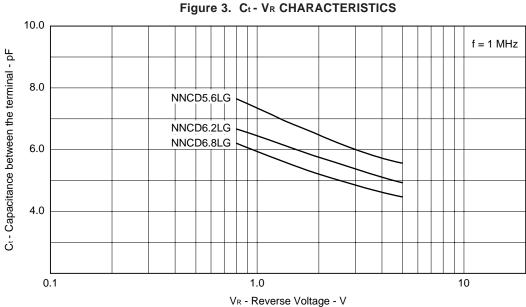
TYPICAL CHARACTERISTICS ($T_A = 25^{\circ}C$)

Figure 1. P - TA RATING

P - Power Dissipation - mW T_A - Ambient Temperature - °C

Figure 2. It - VBR CHARACTERISTICS (A - K1, A - K2, A - K3, A - K4)





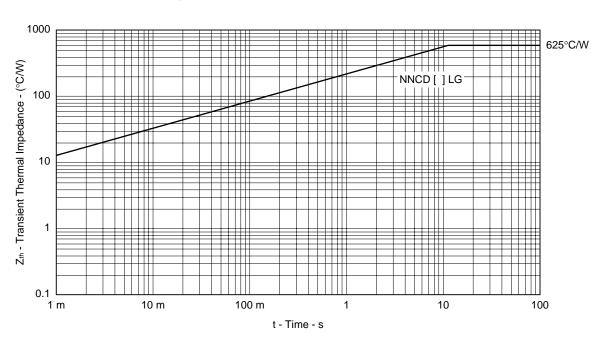
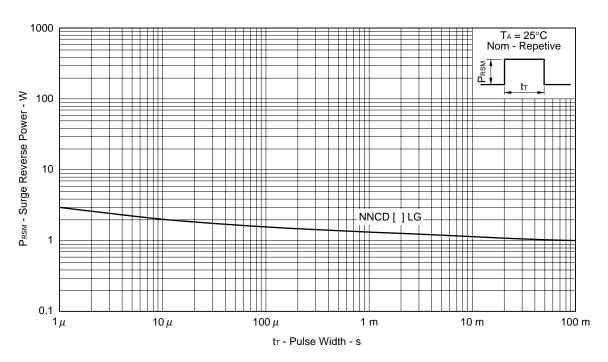


Figure 4. TRANSIENT THERMAL IMPEDANCE







REFERENCE

| Document | Document No. | | |
|---|--------------|--|--|
| NEC semiconductor device reliability/quality control system | C11745E | | |
| NEC semiconductor device reliability/quality control system | MEI - 1201 | | |
| Quality grade on NEC semiconductor device | C11531E | | |
| Semiconductor device mounting technology manual | C10535E | | |

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Anti-radioactive design is not implemented in this product.